Features

- **Single 3-V Supply Voltage**
- **High Power-added Efficient Power Amplifier (P_{out} Typically 23 dBm)**
- **Ramp-controlled Output Power**
- **Low-noise Preamplifier (NF Typically 2.1 dB)**
- **Biasing for External PIN Diode T/R Switch**
- **Current-saving Standby Mode**
- **Few External Components**
- **Packages:**
  - **PSSO20**
  - **QFN20 with Extended Performance**

Electrostatic sensitive device.
Observe precautions for handling.

Bluetooth™/ISM 2.4-GHz Front-End IC

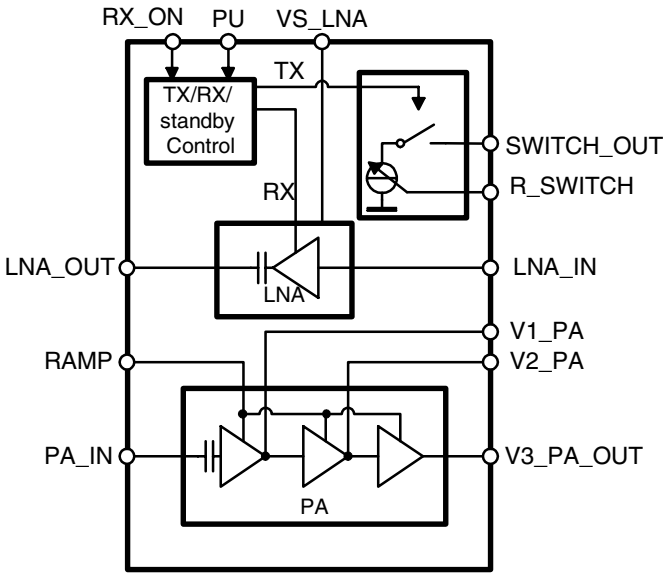
T7024

Description

The T7024 is a monolithic SiGe transmit/receive front-end IC with power amplifier, low-noise amplifier and T/R switch driver. It is especially designed for operation in TDMA systems like Bluetooth™ and WDCT.

Due to the ramp-control feature and a very low quiescent current, an external switch transistor for V_S is not required.

Figure 1. Block Diagram



4533D–BLURF–01/04

Pin Configuration

Figure 2. Pinning PSSO20

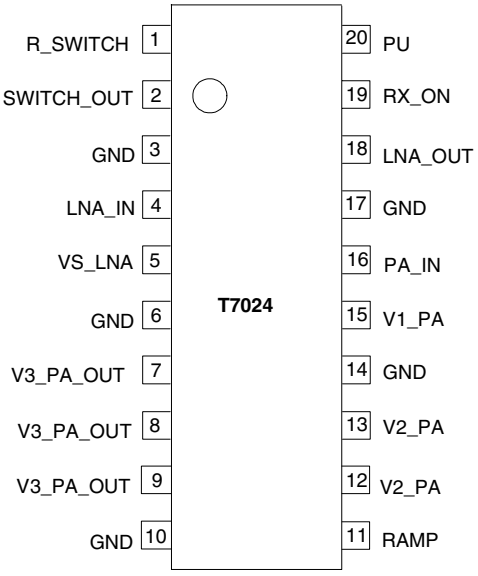
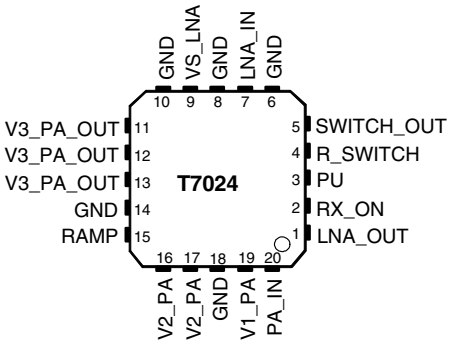


Figure 3. Pinning QFN20



Pin Description

Pins PSSO20	Pins QFN20	Symbol	Function
1	4	R_SWITCH	Resistor to GND sets the PIN diode current
2	5	SWITCH_OUT	Switched current output for PIN diode
3	6	GND	Ground
4	7	LNA_IN	Low-noise amplifier input
5	9	VS_LNA	Supply voltage input for low-noise amplifier
6	8	GND	Ground
7	11	V3_PA_OUT	Inductor to power supply and matching network for power amplifier output
8	12	V3_PA_OUT	Inductor to power supply and matching network for power amplifier output
9	13	V3_PA_OUT	Inductor to power supply and matching network for power amplifier output
10	10	GND	Ground
11	15	RAMP	Power ramping control input
12	16	V2_PA	Inductor to power supply for power amplifier
13	17	V2_PA	Inductor to power supply for power amplifier
14	14	GND	Ground
15	19	V1_PA	Supply voltage for power amplifier
16	20	PA_IN	Power amplifier input
17	18	GND	Ground
18	1	LNA_OUT	Low-noise amplifier output
19	2	RX_ON	RX active high
20	3	PU	Power-up active high
Slug	Slug	GND	Ground

Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Parameters	Symbol	Value	Unit
Supply voltage Pins VS_LNA, V1_PA, V2_PA, V3_PA_OUT	V_S	6	V
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-40 to +125	°C
RF input power LNA	P_{inLNA}	5	dBm
RF input power PA	P_{inPA}	10	dBm

Thermal Resistance

Parameters	Symbol	Value	Unit
Junction ambient PSSOP20, slug soldered on PCB	R_{thJA}	19	K/W
Junction ambient QFN20, slug soldered on PCB	R_{thJA}	27	K/W

Handling

Do not operate this part near strong electrostatic fields. This IC meets class 1 ESD test requirement (HBM in accordance to EIA/JESD22-A114-A (October 97) and class A ESD test requirement (MM) in accordance to EIA/JESD22-A115A.

Operating Range

All voltages are referred to ground (pins GND and slug). Power supply points are VS_LNA, V1_PA, V2_PA, V3_PA_OUT. The table represents the sum of all supply currents depending on the TX/RX mode.

Parameters		Symbol	Min.	Typ.	Max.	Unit
Supply voltage Pins V1_PA, V2_PA and V3_PA_OUT		V_S	2.7	3.0	4.6	V
Supply voltage	Pin VS_LNA	V_S	2.7	3.0	5.5	V
Supply current TX Supply current RX	PSSO20 QFN20	I_S I_S I_S		190 165 8		mA mA mA
Standby current	PU = 0	$I_{S\_standby}$		10		µA
Ambient temperature		T_{amb}	-25	+25	+85	°C

Electrical Characteristics

Test conditions (unless otherwise specified): V_S = 3.0 V, T_{amb} = 25°C

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Power Amplifier(1)						
Supply voltage	Pins V1_PA, V2_PA, V3_PA_OUT	V_S	2.7	3.0	4.6	V
Supply current	TX PSSO20 TX QFN20	I_{S_TX} I_{S_TX}		190 165		mA mA
	RX (PA off), $V_{RAMP} \leq$0.1 V	I_{S_RX}			10	µA
Standby current	Standby	$I_{S\_standby}$			10	µA
Frequency range	TX	f	2.4		2.5	GHz
Gain-control range	TX	ΔGp	60	42		dB
Power gain maximum	TX, Pin PA_IN to V3_PA_OUT	Gp	28	30	33	dB
Power gain minimum	TX, Pin PA_IN to V3_PA_OUT	Gp	-40		-17	dB
Ramping voltage maximum	TX, power gain (maximum) Pin RAMP	$V_{RAMP\ max}$	1.7	1.75	1.83	V
Ramping voltage minimum	TX, power gain (minimum) Pin RAMP	$V_{RAMP\ min}$		0.1		V
Ramping current maximum	TX, V_{RAMP} = 1.75 V, Pin RAMP	$I_{RAMP\ max}$			0.5	mA
Power-added efficiency	TX PSSO20 TX QFN20	PAE PAE	30 35	35 40		% %
Saturated output power	TX, input power = 0 dBm referred to Pins V3_PA_OUT	P_{sat}	22	23	24	dBm
Input matching(2)	TX, Pin PA_IN	Load VSWR		<1.5:1		
Output matching(2)	TX, Pins V3_PA_OUT	Load VSWR		<1.5:1		
Harmonics at P_{sat} = 23 dBm	TX, Pins V3_PA_OUT	2 fo			-30	dBc
	TX, Pins V3_PA_OUT	3 fo			-30	dBc
T/R Switch Driver (Current Programming by External Resistor from R_SWITCH to GND)						
Switch-out current output	Standby, Pin SWITCH_OUT	$I_{S\_O\_standby}$			1	µA
	RX	$I_{S\_O\_RX}$			1	µA
	TX at 100 Ω	$I_{S\_O\_100}$		1.7		mA
	TX at 1.2 kΩ	$I_{S\_O\_1k2}$		7		mA
	TX at 33 kΩ	$I_{S\_O\_33k}$		17		mA
	TX at ∞	$I_{S\_O\_R}$		19		mA
Low-noise Amplifier(3)						
Supply voltage	All, Pin VS_LNA	V_S	2.7	3.0	5.5	V
Supply current	RX	I_S		8	9	mA

Notes:
1. Power amplifier shall be unconditionally stable, maximum duty cycle 100%, true CW operation, maximum load mismatch and duration: load VSWR = 10:1 (all phases) 10 s, Z_G = 50 Ω
2. With external matching network, load impedance 50 Ω
3. Low-noise amplifier shall be unconditionally stable.
4. With external matching components.
5. LNA gain can be adjusted with RX_ON voltage according to Figure 19 on page 11. Please note, that for RX_ON below 1.4 V the T/R switch driver switches to TX mode.

Electrical Characteristics (Continued)

Test conditions (unless otherwise specified): V_S = 3.0 V, T_{amb} = 25°C

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Supply current (LNA and control logic)	TX (control logic active) Pin VS_LNA	I_S			0.5	mA
Standby current	Standby, Pin VS_LNA	$I_{S\_standby}$		1	10	µA
Frequency range	RX	f	2.4		2.5	GHz
Power gain(5)	RX, Pin LNA_IN to LNA_OUT	Gp	15	16	19	dB
Noise figure	RX, PSSO20 RX QFN20	NF NF		2.5 2.1	2.8 2.3	dB dB
Gain compression	RX, referred to Pin LNA_OUT	O1dB	-9	-7	-6	dBm
3rd-order input interception point	RX	IIP3	-16	-14	-13	dBm
Input matching(4)	RX, Pin LNA_IN	VSWRin			2:1	
Output matching(4)	RX Pin LNA_OUT	VSWRout			2:1	
Logic Input Levels (RX_ON, PU)(5)						
High input level	= '1' Pins RX_ON and PU	V_{iH}	2.4		$V_{S, LNA}$	V
Low input level	= '0'	V_{iL}	0		0.5	V
High input current	= '1' V_{iH} = 2.4 V	I_{iH}		40	60	µA
Low input current	= '0'	I_{iL}			0.2	µA

Notes:
1. Power amplifier shall be unconditionally stable, maximum duty cycle 100%, true CW operation, maximum load mismatch and duration: load VSWR = 10:1 (all phases) 10 s, Z_G = 50 Ω
2. With external matching network, load impedance 50 Ω
3. Low-noise amplifier shall be unconditionally stable.
4. With external matching components.
5. LNA gain can be adjusted with RX_ON voltage according to Figure 19 on page 11. Please note, that for RX_ON below 1.4 V the T/R switch driver switches to TX mode.

Control Logic for LNA and T/R Switch Driver

Operation Mode	PU	RX_ON
Standby	0	0
TX	1	0
RX	1	1

Typical Operating Characteristics

Figure 4. LNA (PSSO20): Gain and Noise Figure versus Frequency

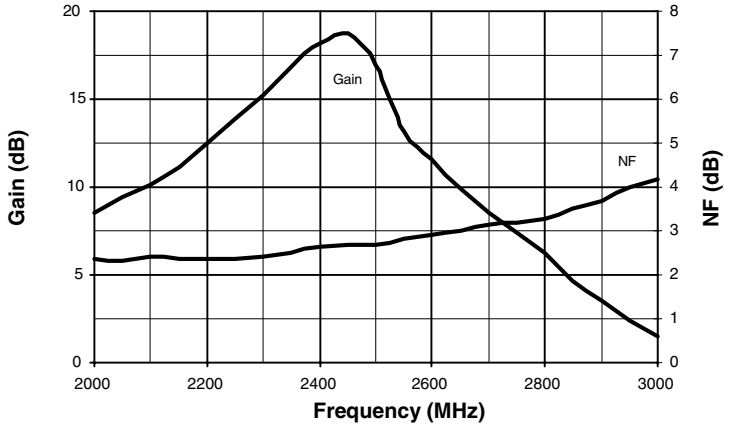


Figure 5. LNA (N20): Gain and Noise Figure versus Frequency

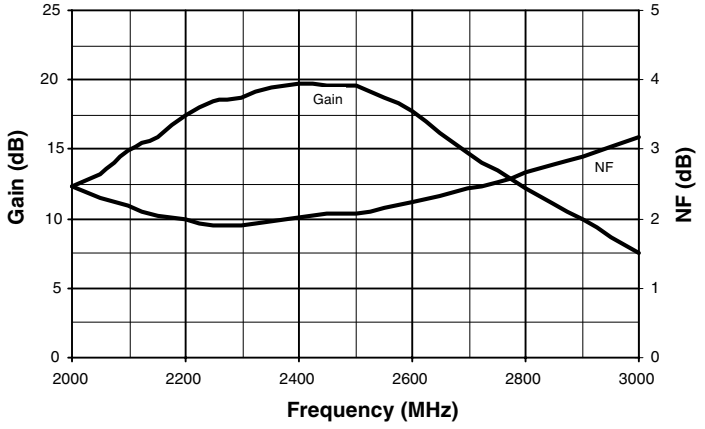


Figure 6. LNA: NF and Gain versus Temperature

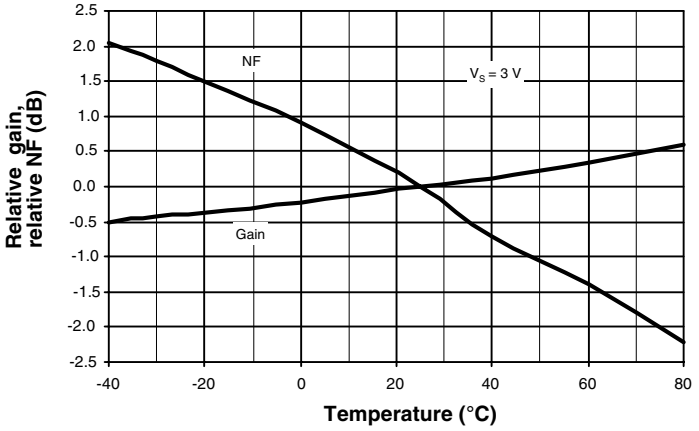


Figure 7. LNA: Typical Switch-out Current versus R_{switch}

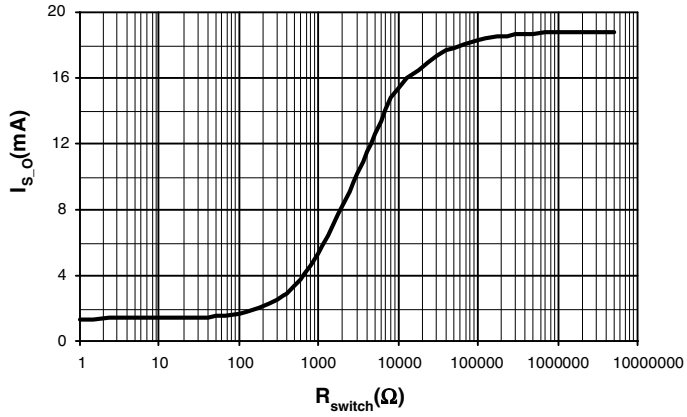


Figure 8. PA (PSSO20): Output Power and PAE versus Supply

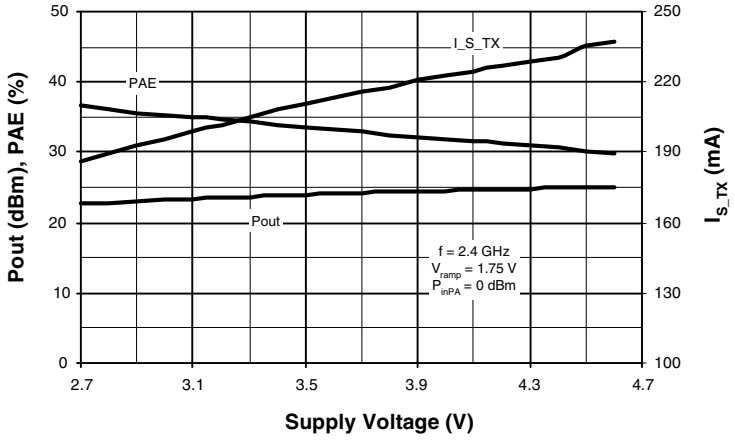


Figure 9. PA (PSSO20): Output Power and PAE versus Ramp Voltage

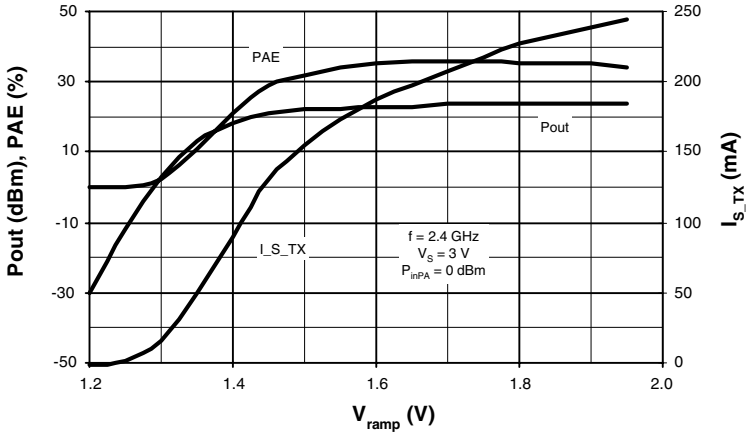


Figure 10. PA (PSSO20): Output Power and PAE versus Input Power

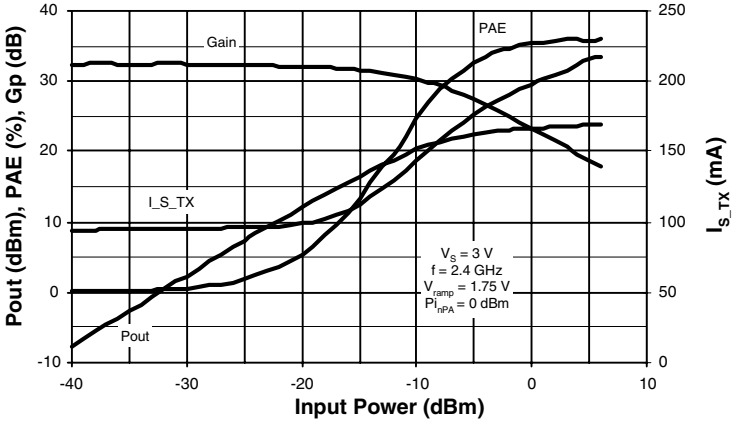


Figure 11. PA (PSSO20): Output Power and PAE versus Frequency

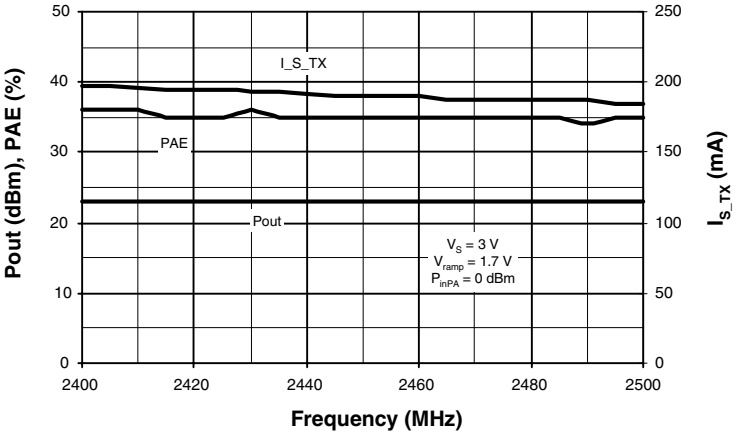


Figure 12. PA (QFN20): Output Power and PAE versus Supply Voltage

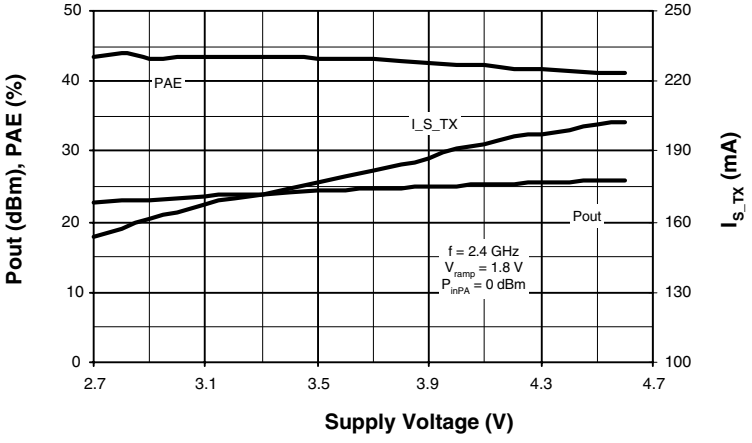


Figure 13. PA (QFN20) Output Power and PAE versus Ramp Voltage

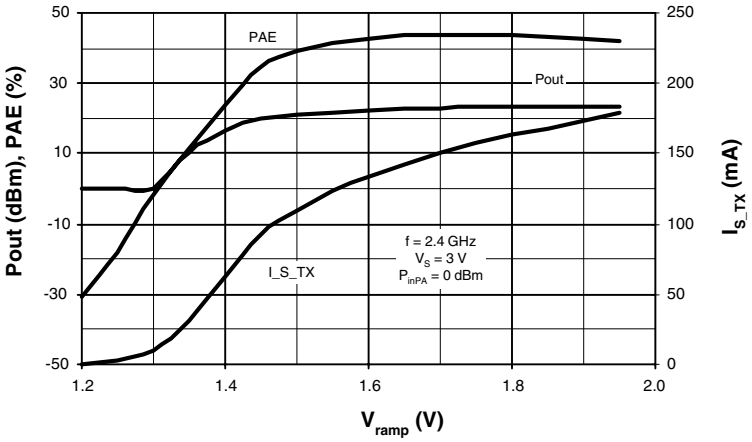


Figure 14. PA (QFN20): Output Power and PAE versus Input Power

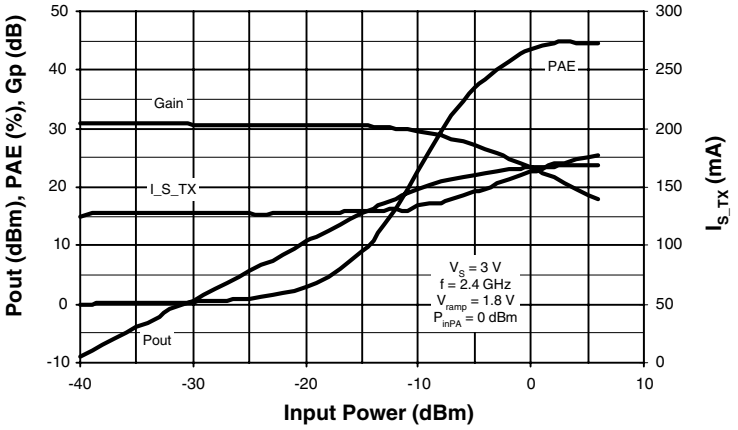


Figure 15. PA (QFN20): Output Power and PAE versus Frequency

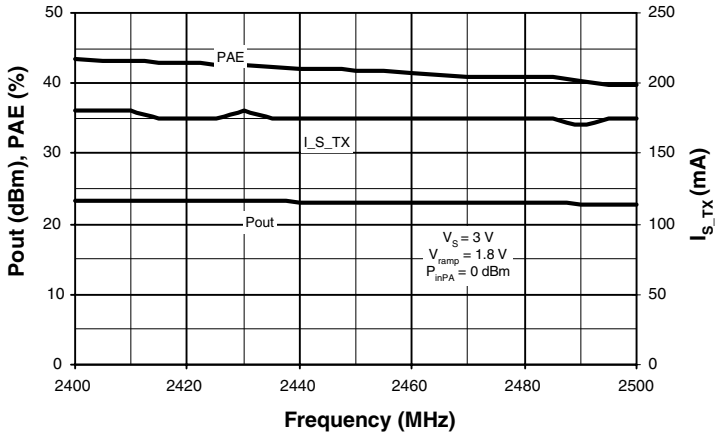


Figure 16. LNA: Supply Current versus Temperature

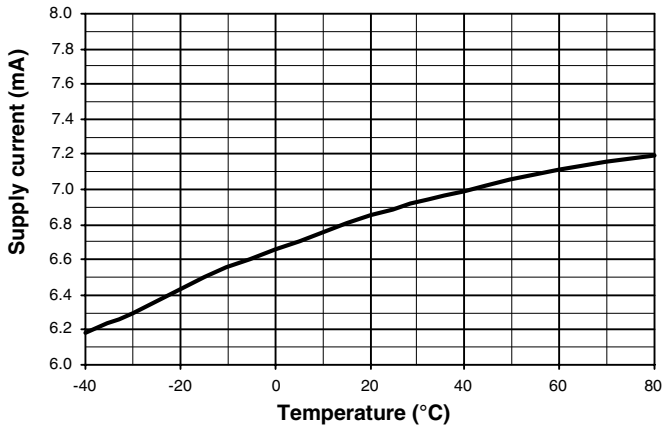


Figure 17. PA (PSSO20): Supply Current versus I_{ramp} and Temperature

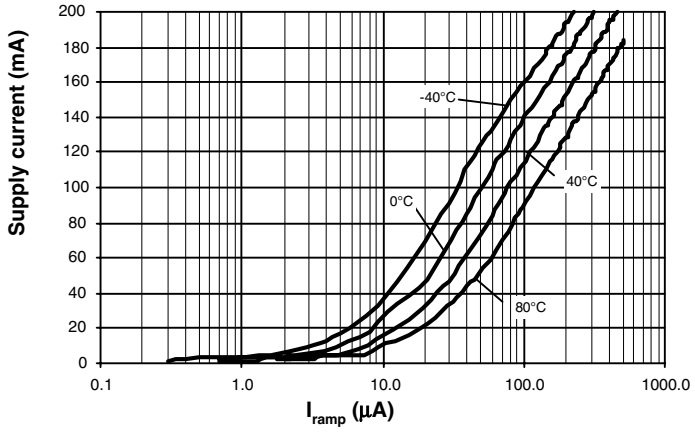


Figure 18. PA (PSSO20, QFN20): P_{out} versus V_{ramp} and Temperature

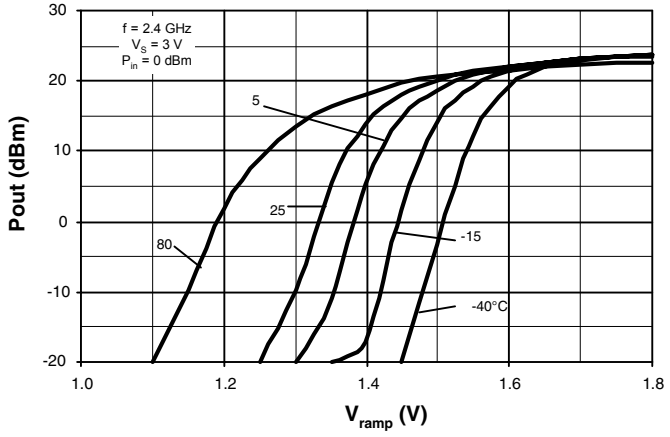
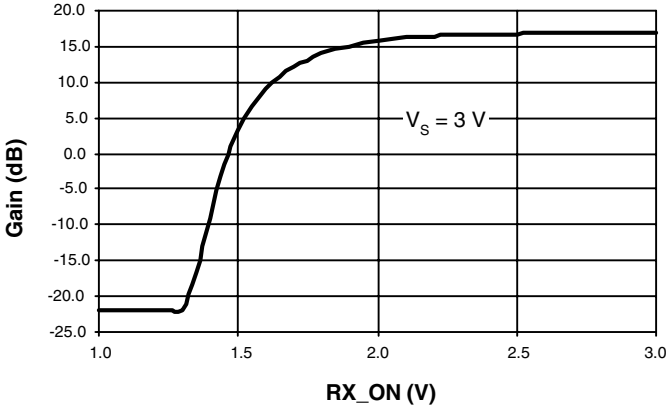


Figure 19. (PSSO20, QFN20): LNA Gain (dB) versus RX_ON (V)



Input/Output Circuits

Figure 20. Input Circuit PA_IN/V1_PA

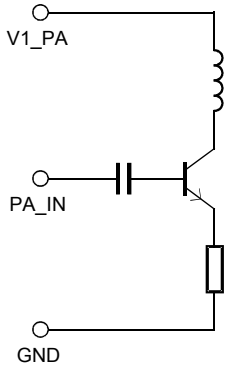


Figure 21. Input Circuit RAMP/V1_PA

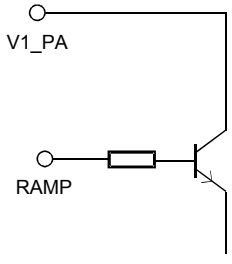


Figure 22. Input Circuit V2_PA

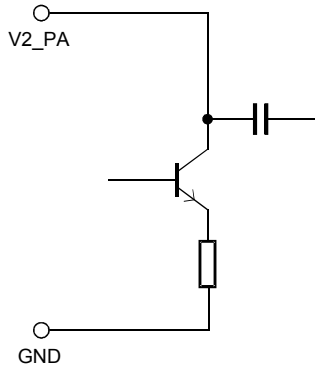


Figure 23. Input/Output Circuit V3_PA_OUT

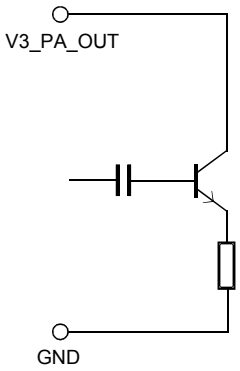


Figure 24. Input Circuit SWITCH_OUT/R_SWITCH

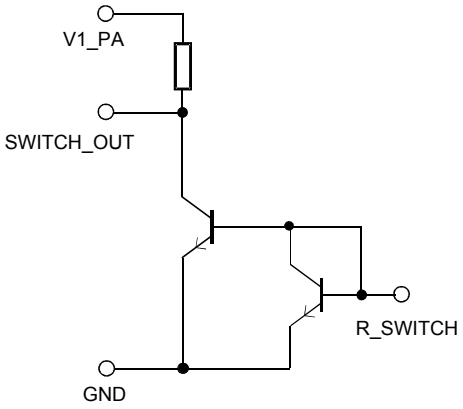


Figure 25. Input Circuit LNA_IN/VS_LNA

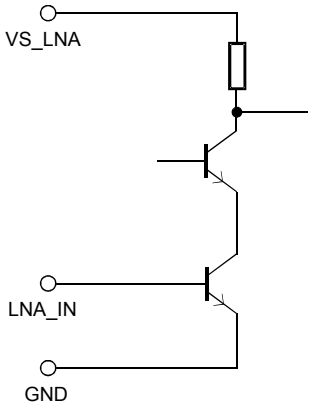


Figure 26. Input Circuit PU/RX_ON

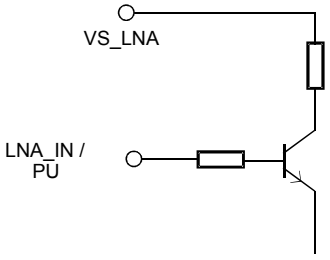


Figure 27. Output Circuit LNA_OUT

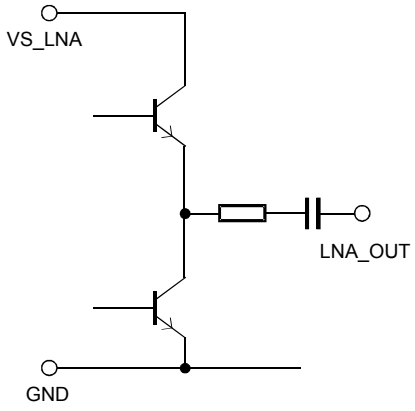


Figure 28. Typical Application T7024 (PSSO20 Package)

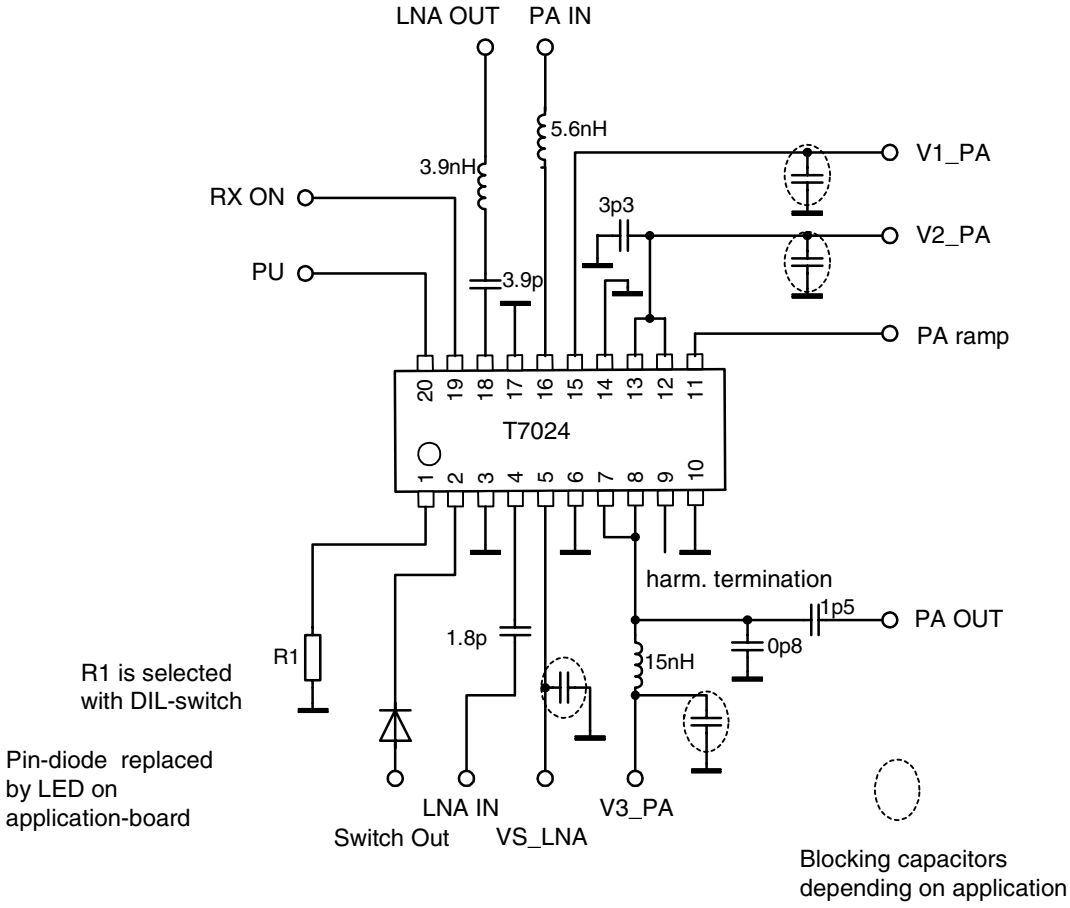
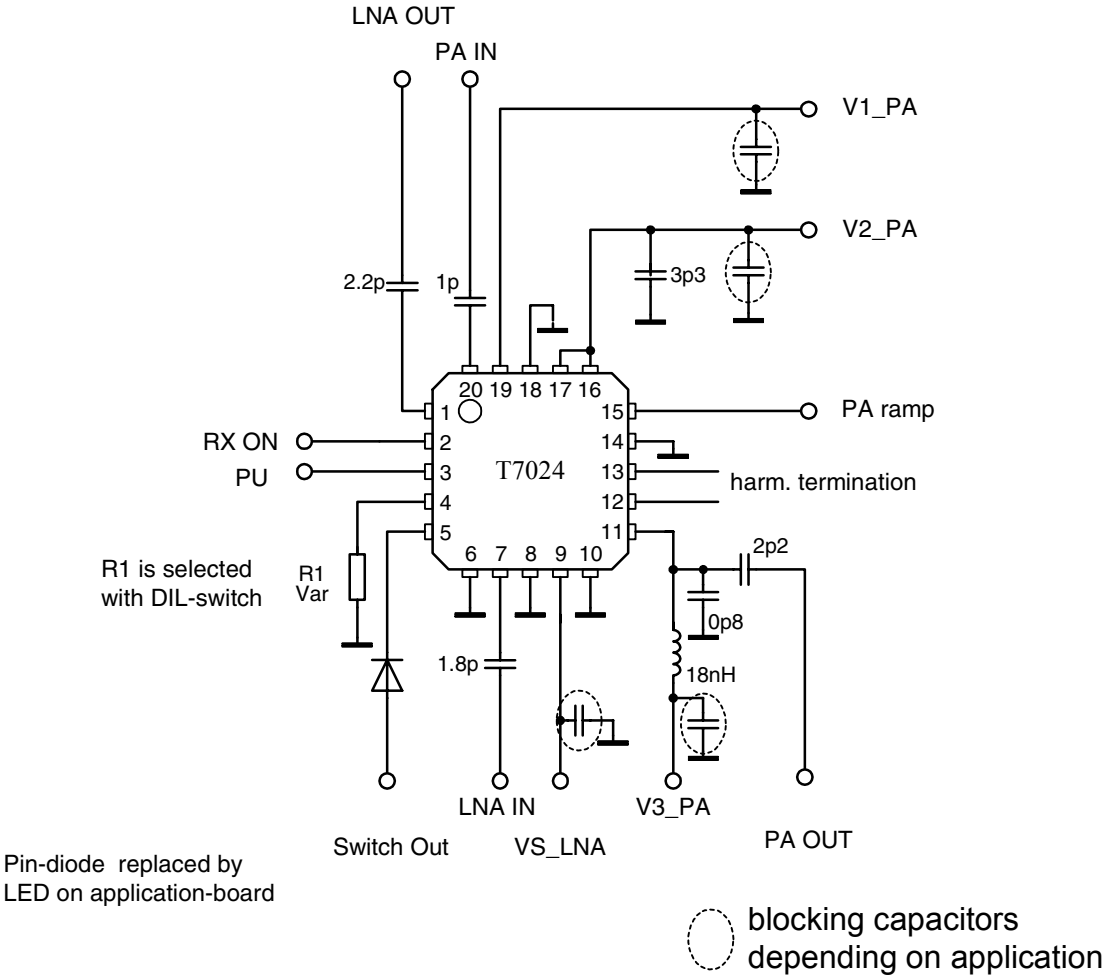


Figure 29. Typical Application T7024 (QFN20 Package)

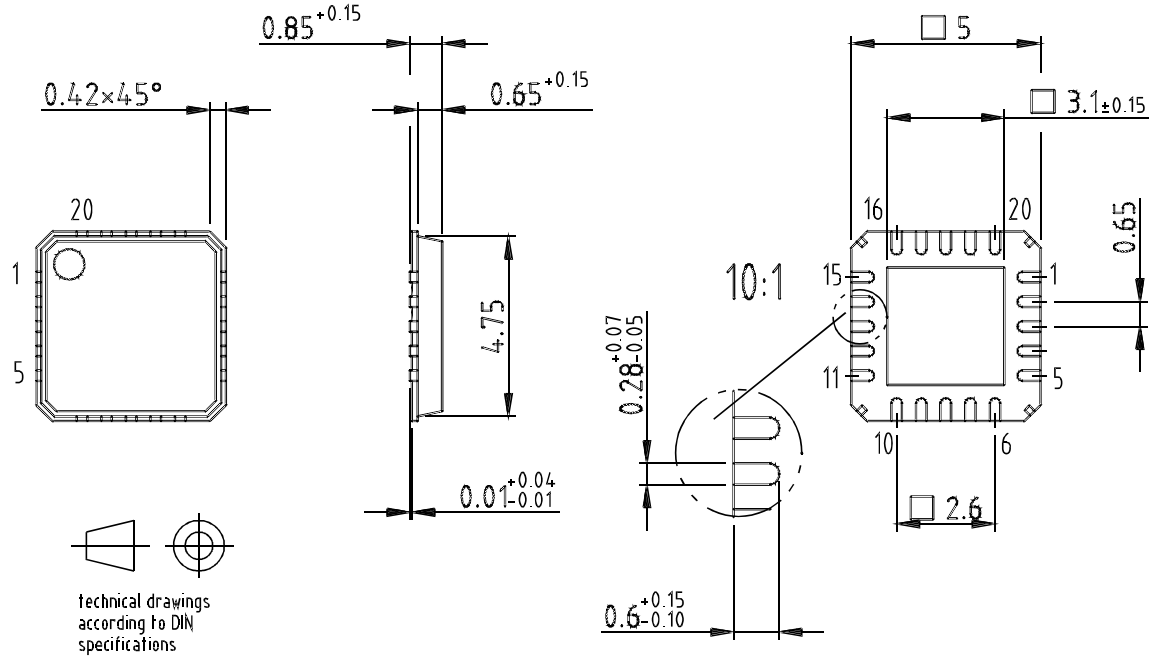


Ordering Information

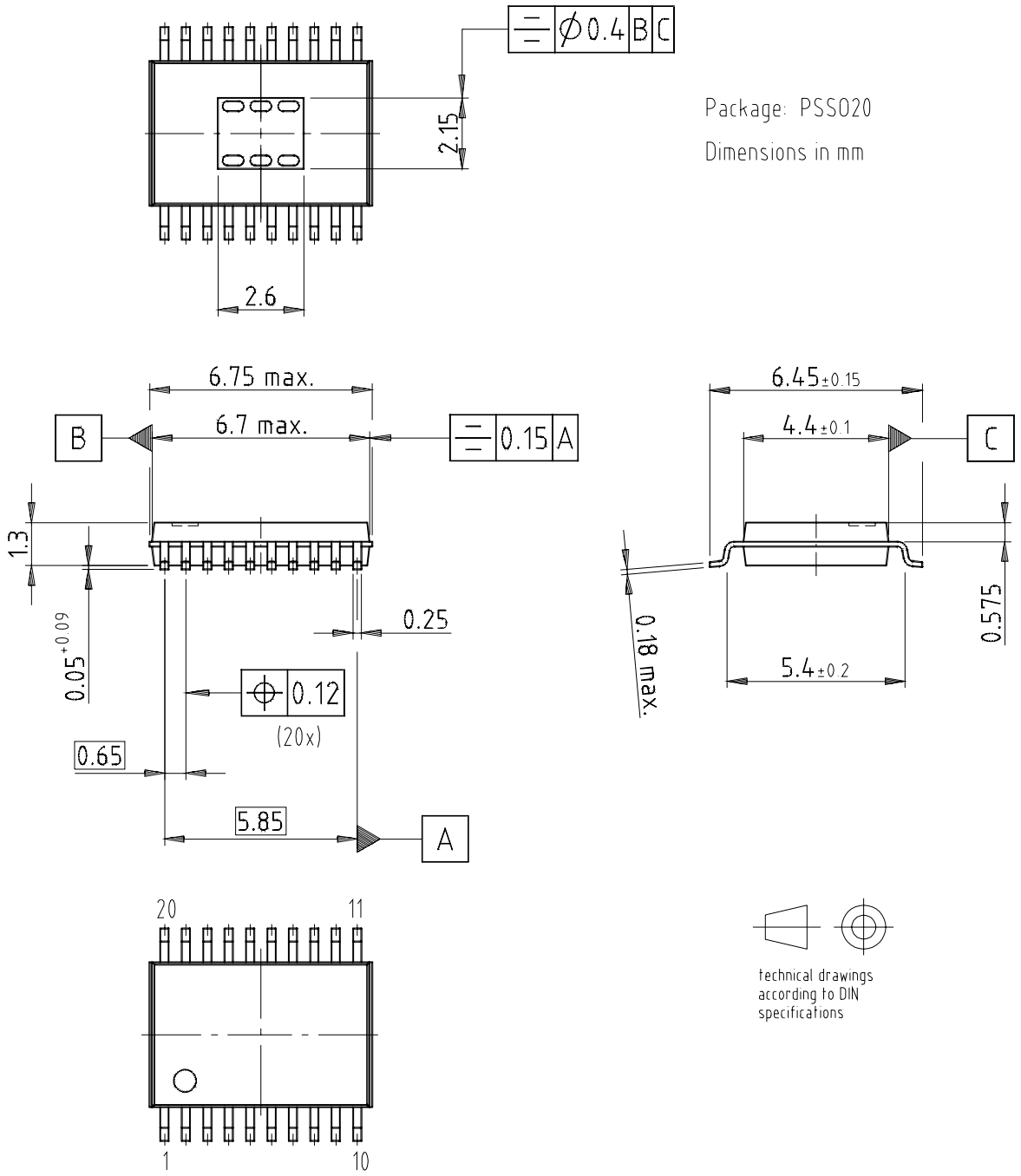
Extended Type Number	Package	Remarks	MOQ
T7024-TRS	PSSO20	Tube	830 pcs.
T7024-TRQ	PSSO20	Taped and reeled	4000 pcs.
T7024-PGP	QN20	Taped and reeled	1500 pcs.
T7024-PGQ	QFN20	Taped and reeled	6000 pcs.

Package Information

Package: QFN 20 - 5x5
Exposed pad 3.1x3.1
(acc. JEDEC OUTLINE No. MO-220)
Dimensions in mm



Drawing-No.: 6.543-5069.02-4
Issue: 3; 24.01.03



Drawing-No.: 6.543-5078.01-4
Issue: 1; 05.06.01

Atmel Corporation

2325 Orchard Parkway
San Jose, CA 95131, USA
Tel: 1(408) 441-0311
Fax: 1(408) 487-2600

Regional Headquarters

Europe
Atmel Sarl
Route des Arsenaux 41
Case Postale 80
CH-1705 Fribourg
Switzerland
Tel: (41) 26-426-5555
Fax: (41) 26-426-5500

Asia
Room 1219
Chinachem Golden Plaza
77 Mody Road Tsimshatsui
East Kowloon
Hong Kong
Tel: (852) 2721-9778
Fax: (852) 2722-1369

Japan
9F, Tonetsu Shinkawa Bldg.
1-24-8 Shinkawa
Chuo-ku, Tokyo 104-0033
Japan
Tel: (81) 3-3523-3551
Fax: (81) 3-3523-7581

Atmel Operations

Memory
2325 Orchard Parkway
San Jose, CA 95131, USA
Tel: 1(408) 441-0311
Fax: 1(408) 436-4314

Microcontrollers
2325 Orchard Parkway
San Jose, CA 95131, USA
Tel: 1(408) 441-0311
Fax: 1(408) 436-4314

La Chantrerie
BP 70602
44306 Nantes Cedex 3, France
Tel: (33) 2-40-18-18-18
Fax: (33) 2-40-18-19-60

ASIC/ASSP/Smart Cards
Zone Industrielle
13106 Rousset Cedex, France
Tel: (33) 4-42-53-60-00
Fax: (33) 4-42-53-60-01

1150 East Cheyenne Mtn. Blvd.
Colorado Springs, CO 80906, USA
Tel: 1(719) 576-3300
Fax: 1(719) 540-1759

Scottish Enterprise Technology Park
Maxwell Building
East Kilbride G75 0QR, Scotland
Tel: (44) 1355-803-000
Fax: (44) 1355-242-743

RF/Automotive
Theresienstrasse 2
Postfach 3535
74025 Heilbronn, Germany
Tel: (49) 71-31-67-0
Fax: (49) 71-31-67-2340

1150 East Cheyenne Mtn. Blvd.
Colorado Springs, CO 80906, USA
Tel: 1(719) 576-3300
Fax: 1(719) 540-1759

Biometrics/Imaging/Hi-Rel MPU/
High Speed Converters/RF Datacom
Avenue de Rochepleine
BP 123
38521 Saint-Egreve Cedex, France
Tel: (33) 4-76-58-30-00
Fax: (33) 4-76-58-34-80

Literature Requests
www.atmel.com/literature

4533D–BLURF–01/04